

469.

标题: Ba(Zn<sub>1/3</sub>Ta<sub>2/3</sub>)O<sub>3</sub> perovskite ceramics doped with Nb<sup>5+</sup>, Ce<sup>4+</sup> or Yb<sup>3+</sup>

作者: Busuioc, C (Busuioc, C.); Jinga, SI (Jinga, S. I.); Stoleriu, S (Stoleriu, S.); Nedelcu, L (Nedelcu, L.); Andronescu, E (Andronescu, E.)

来源出版物: JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS 卷: 14

期: 3-4 页: 238-244 出版年: MAR-APR 2012

在 Web of Science 中的被引频次: 0

被引频次合计: 0

引用的参考文献数: 15

摘要: Ba(Zn<sub>1/3</sub>Ta<sub>2/3</sub>)O<sub>3</sub> (BZT) perovskite material has stimulated a large interest due to its excellent dielectric properties in microwave frequency range, enabling the miniaturization of communications devices. In this work, BZT ceramics were prepared by the conventional solid-state reaction method, being doped with Nb<sup>5+</sup>, Ce<sup>4+</sup> or Yb<sup>3+</sup>. BZT resonators were compositional, structural, morphological and electrical characterized. The influence of the dopants and sintering temperature on the microwave dielectric properties of BZT samples was investigated. The resonator doped with 0.5 mol% Nb<sub>2</sub>O<sub>5</sub> and sintered at 1600 degrees C / 2 h exhibits the best dielectric behaviour:  $\epsilon(r)$  similar to 25.9 and  $Q_{xf}$  similar to 159 THz.

入藏号: WOS:000304429900009

语种: English

文献类型: Article

作者关键词: Perovskite; Dielectric; Resonator; Microwave

KeyWords Plus: MICROWAVE DIELECTRIC-PROPERTIES; TEMPERATURE; DOPANTS

地址: [Busuioc, C.; Jinga, S. I.; Stoleriu, S.; Andronescu, E.] Univ Politehn Bucuresti, RO-011061 Bucharest, Romania

[Busuioc, C.; Nedelcu, L.] Natl Inst Mat Phys, RO-077125 Magurele, Romania

通讯作者地址: Jinga, SI (通讯作者), Univ Politehn Bucuresti, RO-011061 Bucharest, Romania

电子邮件地址: sorinjonjinga@yahoo.com

出版商: NATL INST OPTOELECTRONICS

出版商地址: 1 ATOMISTILOR ST, PO BOX MG-5, BUCHAREST-MAGURELE 76900, ROMANIA

Web of Science 分类: Materials Science, Multidisciplinary; Optics; Physics, Applied

学科类别: Materials Science; Optics; Physics

IDS 号: 947KW

ISSN: 1454-4164

29 字符的来源出版物名称缩写: J OPTOELECTRON ADV M

ISO 来源出版物缩写: J. Optoelectron. Adv. Mater.

来源出版物页码计数: 7